Unit: mm

TOSHIBA Transistor Silicon NPN Epitaxial Type

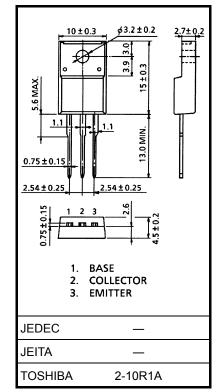
# 2SD1947A

### High-Current Switching Applications Lamp, Solenoid Drive Applications

- High DC current gain:  $h_{FE} = 500$  to 1500 (IC = 1 A)
- Low collector saturation voltage:  $V_{CE}$  (sat) = 0.3 V (max) (I<sub>C</sub> = 5 A)

#### Absolute Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V <sub>CBO</sub>	100	V	
Collector-emitter voltage		V <sub>CEO</sub>	100	V	
Emitter-base voltage		V <sub>EBO</sub>	7	V	
Collector current	DC	Ι <sub>C</sub>	10	А	
	Pulse	I <sub>CP</sub>	15	~	
Base current		Ι <sub>Β</sub>	2	А	
Collector power dissipation	Ta = 25°C	Pc	2.0	W	
	Tc = 25°C	ГC	40		
Junction temperature		Тј	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 1.7 g (typ.)

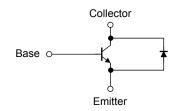
Note: Using continuously under heavy loads (e.g. the application of high

temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage\_etc.) are within the absolute maximum ratings.

temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

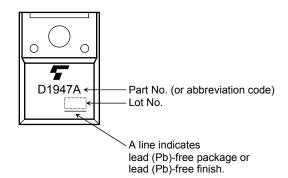
#### **Equivalent Circuit**



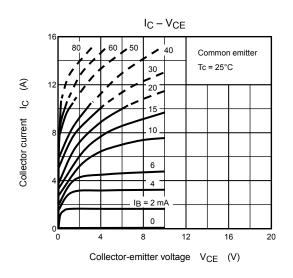
Electrical Characteristics (Tc = 25°C)

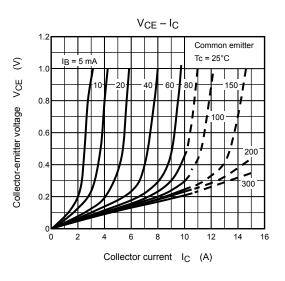
Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off of	current	I <sub>CBO</sub>	V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0	_	_	10	μA
Emitter cut-off current		I <sub>EBO</sub>	V <sub>EB</sub> = 7 V, I <sub>C</sub> = 0	_	_	10	μA
Collector-emitter breakdown voltage		V (BR) CEO	I <sub>C</sub> = 50 mA, I <sub>B</sub> = 0	100	_	_	V
DC current gain		h <sub>FE (1)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 1 A	500	_	1500	
		h <sub>FE (2)</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 A	150	_	_	
Collector-emitter saturation voltage		V <sub>CE (sat)</sub>	I <sub>C</sub> = 5 A, I <sub>B</sub> = 0.05 A		_	0.3	V
Base-emitter saturation voltage		V <sub>BE (sat)</sub>	I <sub>C</sub> = 5 A, I <sub>B</sub> = 0.05 A		_	1.2	V
Collector-emitter forward voltage		V <sub>ECF</sub>	I <sub>E</sub> = 5 A, I <sub>B</sub> = 0		_	2.0	V
Transition frequency		fT	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 1 A	_	70	_	MHz
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	160	_	pF
-	Turn-on time	t <sub>on</sub>	Output Input $ B_1 $ $20 \ \mu s$ $ B_2 $ $M \rightarrow V_{CC} = 30 \ V$ $ B_1 = - B_2 = 0.05 \ A, \ duty \ cycle \le 1\%$	_	0.5	_	
	Storage time	t <sub>stg</sub>		_	6.0	_	μs
	Fall time	t <sub>f</sub>		_	1.0	_	

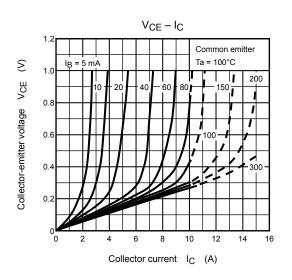
## Marking

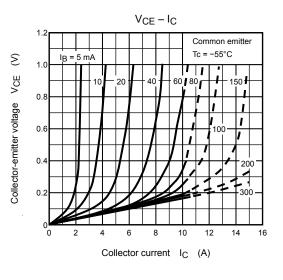


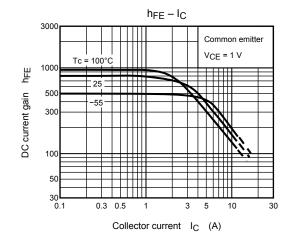
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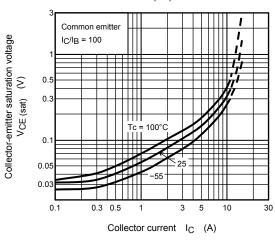




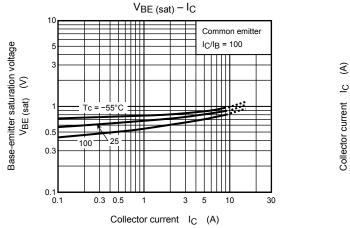


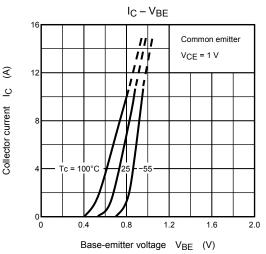


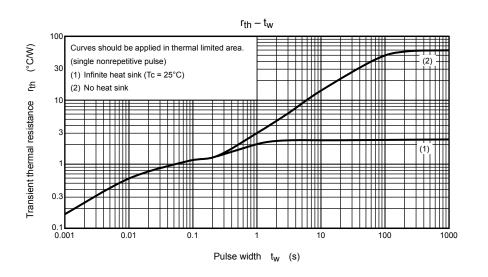
V<sub>CE (sat)</sub> – I<sub>C</sub>

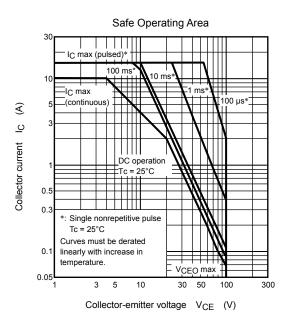


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